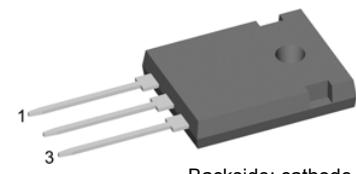
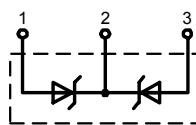


Schottky

High Performance Schottky Diode
Low Loss and Soft Recovery
Common Cathode

V_{RRM} = 30 V**I_{FAV} = 2x 30 A****V_F = 0.47 V****Part number****DSB 60 C 30HB**

Backside: cathode

Features / Advantages:

- Very low V_f
- Extremely low switching losses
- Low I_{rm}-values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package:

TO-247AD

- Industry standard outline
- Epoxy meets UL 94V-0
- RoHS compliant

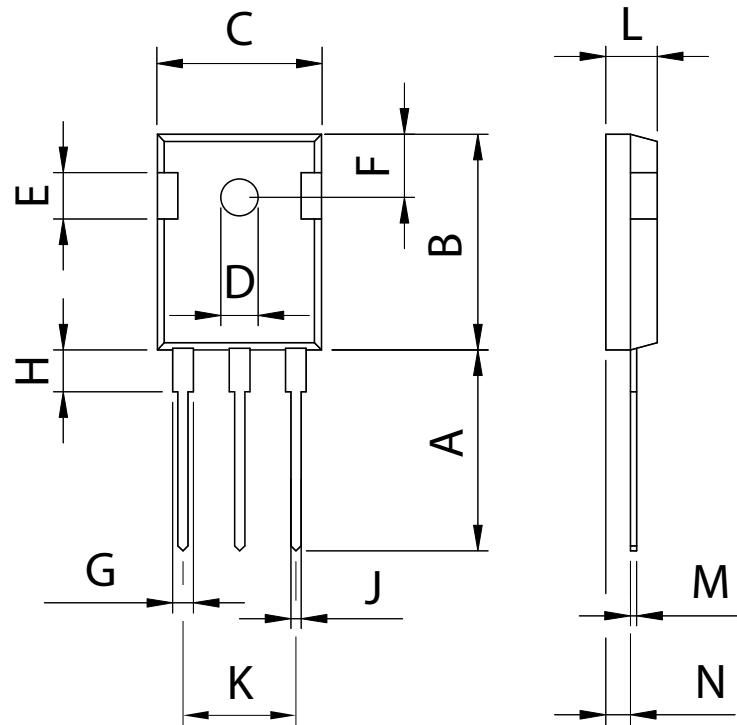
Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	Unit
V _{RRM}	max. repetitive reverse voltage	T _{vJ} = 25 °C			30	V
I _R	reverse current	V _R = 30 V T _{vJ} = 25 °C V _R = 30 V T _{vJ} = 100 °C			20	mA
					80	mA
V _F	forward voltage	I _F = 30 A T _{vJ} = 25 °C I _F = 60 A			0.53	V
		I _F = 30 A T _{vJ} = 125 °C I _F = 60 A			0.71	V
					0.47	V
					0.70	V
I _{FAV}	average forward current	rectangular, d = 0.5	T _c = 125 °C		30	A
V _{F0} r _F	threshold voltage slope resistance } for power loss calculation only		T _{vJ} = 150 °C		0.22	V
					8	mΩ
R _{thJC}	thermal resistance junction to case				0.95	K/W
T _{vJ}	virtual junction temperature		-55		150	°C
P _{tot}	total power dissipation	T _c = 25 °C			130	W
I _{FSM}	max. forward surge current	t _p = 10 ms (50 Hz), sine	T _{vJ} = 45 °C		330	A
C _J	junction capacitance	V _R = tbd V; f = 1 MHz	T _{vJ} = 25 °C	tbd		pF
E _{AS}	non-repetitive avalanche energy	I _{AS} = tbd A; L = 100 μH	T _{vJ} = 25 °C		tbd	mJ
I _{AR}	repetitive avalanche current	V _A = 1.5 · V _R typ.; f = 10 kHz			tbd	A

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
I_{RMS}	RMS current	per pin*			50	A
R_{thCH}	thermal resistance case to heatsink			0.25		K/W
M_D	mounting torque		0.8		1.2	Nm
F_c	mounting force with clip		20		120	N
T_{stg}	storage temperature		-55		150	°C
Weight				6		g

* I_{RMS} is typically limited by: 1. pin-to-chip resistance; or by 2. current capability of the chip.

In case of 1, a common cathode/anode configuration and a non-isolated backside, the whole current capability can be used by connecting the backside.

Outlines TO-247AD



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102